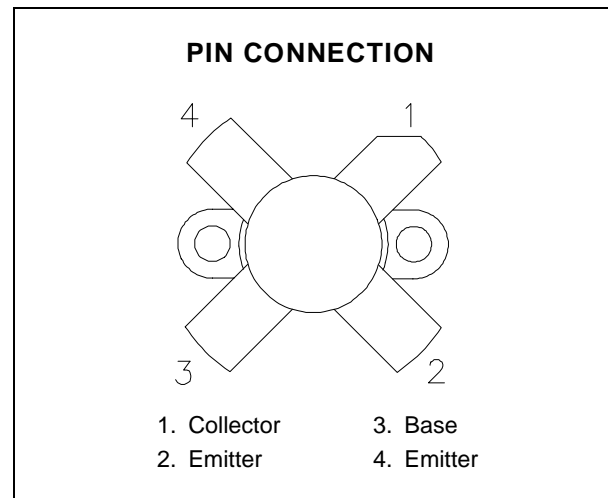
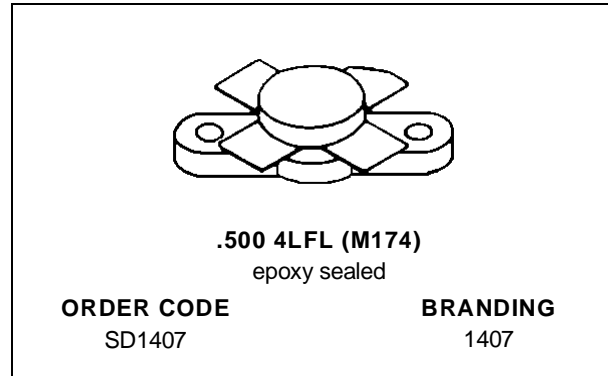


**RF & MICROWAVE TRANSISTORS
HF SSB APPLICATIONS**

- 30 MHz
- 28 VOLTS
- IMD -30 dB
- COMMON EMITTER
- GOLD METALLIZATION
- P_{OUT} = 125 W MIN. WITH 15 dB GAIN


DESCRIPTION

The SD1407 is a 28 V epitaxial silicon NPN planar transistor designed primarily for SSB communications. This device utilizes state-of-the-art diffused emitter ballasting for improved ruggedness and reliability.

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	65	V
V _{CEO}	Collector-Emitter Voltage	36	V
V _{EBO}	Emitter-Base Voltage	4.0	V
I _C	Device Current	20	A
P _{DISS}	Power Dissipation	270	W
T _J	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	- 65 to +150	°C

THERMAL DATA

R _{TH(j-c)}	Junction-Case Thermal Resistance	0.65	°C/W
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SD1407

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV _{CBO}	I _C = 100mA	I _E = 0mA	65	—	—	V
BV _{CES}	I _C = 100mA	V _{BE} = 0V	65	—	—	V
BV _{CEO}	I _C = 100mA	I _B = 0mA	35	—	—	V
BV _{EBO}	I _E = 10mA	I _C = 0mA	4.0	—	—	V
I _{CES}	V _{CE} = 30V	I _E = 0mA	—	—	15	mA
h _{FE}	V _{CE} = 5V	I _C = 5A	10	—	200	—

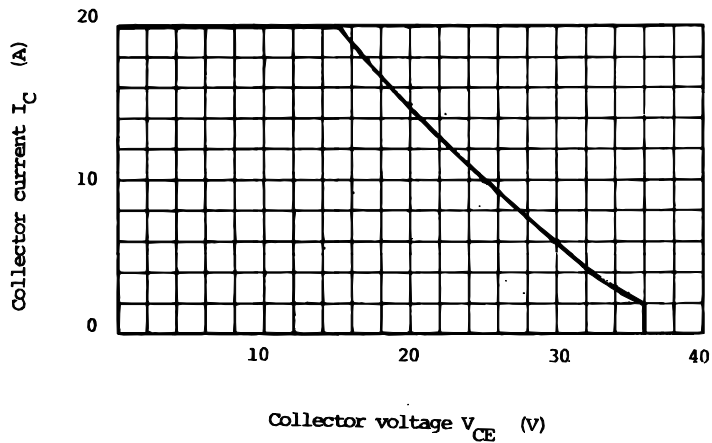
DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P _{OUT}	f = 30 MHz	P _{IN} = 3.95 W	V _{CE} = 28 V	125	—	—	W
G _P	f = 30 MHz	P _{IN} = 3.95 W	V _{CE} = 28 V	15	16	—	dB
IMD*	f = 30 MHz	V _{CE} = 28 V	I _{CQ} = 100 mA	—	-34	-30	dB
C _{OB}	f = 1 MHz	V _{CB} = 30 V		—	250	—	pF

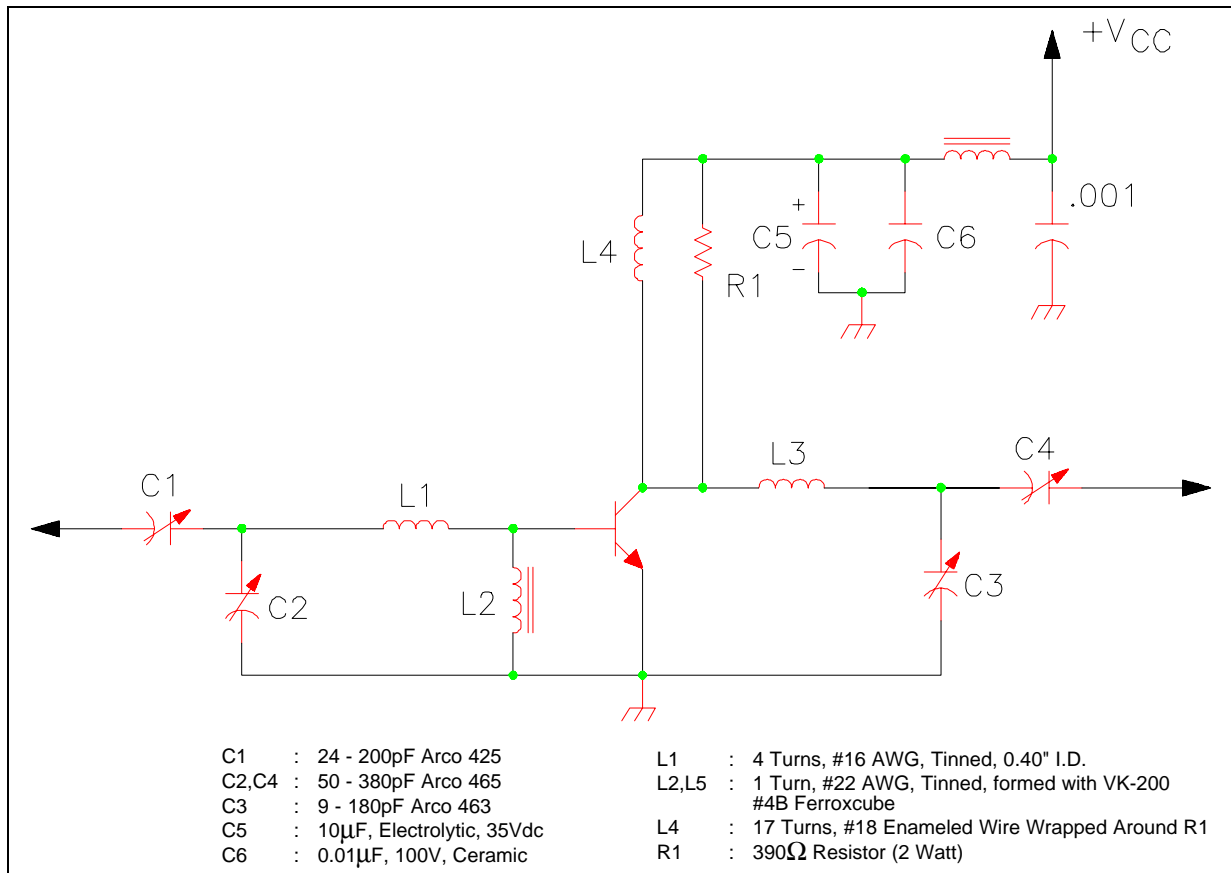
Note: *P_{OUT} = 100W PEP, f₀ = 30 + 30.001 MHz

TYPICAL PERFORMANCE

SAFE OPERATING AREA

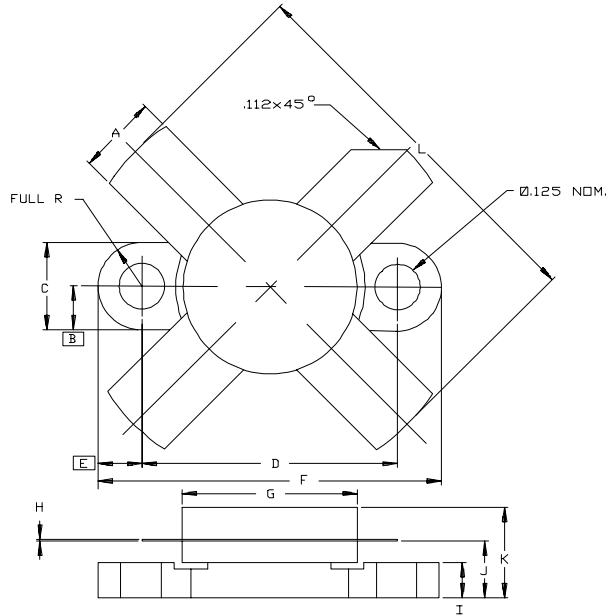


TEST CIRCUIT



PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0174



SGS-THOMSON MICROELECTRONICS		CONT'D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm		
A	.220/5,59	.230/5,84	K	.280/7,11
B	.125/3,18		L	1.050/26,67
C	.245/6,22	.255/6,48		
D	.720/18,28	.730/18,54		
E	.125/3,18			
F	.970/24,64	.980/24,89		
G	.495/12,57	.505/12,83		
H	.003/0,08	.007/0,18		
I	.090/2,29	.110/2,79		
J	.160/4,06	.175/4,45		

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